

## **ABSTRACT OF THE DISCLOSURE**

Disclosed are a semiconductor memory device and a layout method thereof. The device comprises  $km$  memory cell array blocks arranged in the form of  $ak \times m$  matrix, divided by  $x$  block selecting signals and  $y$  block selecting signals, and including a plurality of divided word lines arranged horizontally; a plurality of bit lines for each of the  $km$  memory cell array blocks arranged vertically; a plurality of main word lines for a plurality of bit lines for each of the  $km$  memory cell array blocks arranged horizontally;  $km$  of  $xy$  address word lines above or below the  $km$  memory cell array blocks; a decoder for decoding a corresponding  $x$  block selecting signal among  $x$  block selecting signals generated by decoding the  $x$  block selecting address and  $y$  block selecting signals generated by decoding the  $y$  block address to select corresponding  $m$  of  $xy$  address word lines and for being arranged for each of  $m$  memory cell array blocks arranged horizontally among the  $km$  memory cell array blocks;  $km$  of divided  $y$  address lines arranged vertically from the  $km$  of  $xy$  address word lines to the  $km$  memory cell array blocks; and word line driver for combining the plurality of the main word lines of each of the  $km$  memory cell array blocks and a signal of a corresponding  $xy$  address word line among the  $km$  of  $xy$  address word lines to select the plurality of the divided word lines and for being arranged for each of the  $km$  memory cell array block.

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